

IGBT<sup>3</sup> Chip**FEATURES:**

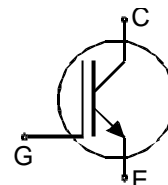
- 1200V Trench & Field Stop technology
- 120µm chip
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling

**This chip is used for:**

- power module

**Applications:**

- drives



Chip Type	V <sub>CE</sub>	I <sub>CN</sub>	Die Size	Package	Ordering Code
SIGC12T120L	1200V	8A	3.54 x 3.5 mm <sup>2</sup>	sawn on foil	Q67050-A4269-A101

**MECHANICAL PARAMETER:**

Raster size	3.54 x 3.5	mm
Emitter pad size	2.03 x 2.03	
Gate pad size	1.1 x 0.7	
Area total / active	12.4 / 6.9	mm <sup>2</sup>
Thickness	120	µm
Wafer size	150	mm
Flat position	0	grd
Max.possible chips per wafer	1200 pcs	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm AlSiCu	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

## MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j=25\text{ °C}$	$V_{CE}$	1200	V
DC collector current, limited by $T_{jmax}$	$I_C$	<sup>1)</sup>	A
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	24	A
Gate emitter voltage	$V_{GE}$	$\pm 20$	V
Operating junction and storage temperature	$T_j, T_{stg}$	-55 ... +150	°C

<sup>1)</sup> depending on thermal properties of assembly

## STATIC CHARACTERISTICS (tested on chip), $T_j=25\text{ °C}$ , unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.5mA$	1200			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=8A$	1.35	1.65	2.05	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=300\mu A, V_{GE}=V_{CE}$	5.0	5.8	6.5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$			1.07	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$			120	nA
Integrated gate resistor	$R_{Gint}$			--		$\Omega$

## ELECTRICAL CHARACTERISTICS (tested at component):

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	$C_{iss}$	$V_{CE}=25V,$		605		pF
Output capacitance	$C_{oss}$	$V_{GE}=0V,$		37		
Reverse transfer capacitance	$C_{rss}$	$f=1MHz$		29		

## SWITCHING CHARACTERISTICS (tested at component), Inductive Load

Parameter	Symbol	Conditions <sup>1)</sup>	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=125\text{ °C}$		0.05		$\mu s$
Rise time	$t_r$	$V_{CC}=600V,$		0.025		
Turn-off delay time	$t_{d(off)}$	$I_C=8A,$		0.35		
Fall time	$t_f$	$V_{GE}=-15/15V,$ $R_G=82\Omega$		0.15		

<sup>1)</sup> values also influenced by parasitic L- and C- in measurement and package.

Die-Size 3540 um x 3500 um

L762b1

3540

2534

249

756

2028

756

248

3500

2514

2028

249

736

515

702

250

2514

736

1107

756

920

2534

249

metal1

imide

1 mm

Flat

**FURTHER ELECTRICAL CHARACTERISTICS:**

This chip data sheet refers to the device data sheet	tbd	
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**DESCRIPTION:**

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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